

Application No. 10/769,204
September 13, 2005
Page 2

P910041DIV

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1-21. (Cancelled)

22. (Currently Amended) A nonvolatile memory on a semiconductor substrate, comprising:

- (a) a prepared semiconductor substrate;
- (b) a plurality of bit lines;
- (c) a plurality of trapping layer block structures; and

(d) a plurality of word lines over corresponding members of the plurality of trapping layer block structures, wherein widths of the trapping layer block structures are greater than widths of the word lines; and

(e) at least one dielectric disposed between the plurality of word lines and trapping layer block structures.

23. (Cancelled)

24. (Currently Amended) The nonvolatile memory of claim 22, wherein the plurality of trapping layer block structures comprises in sequence, a first oxide layer, a nitride layer, and a second oxide layer.

25. (Currently Amended) ~~The nonvolatile memory of claim 22, wherein the plurality of trapping layer block structures overlaps~~ A nonvolatile memory on a semiconductor substrate, comprising:

- (a) a prepared semiconductor substrate;
- (b) a plurality of bit lines;

P910041DIV

Application No. 10/769,204
September 13, 2005
Page 3

(c) a plurality of trapping layer block structures overlapping portions of adjoining members of the plurality of bit lines; and

(d) a plurality of word lines over corresponding members of the plurality of trapping layer block structures, wherein widths of the trapping layer block structures are greater than widths of the word lines.

26. (New) The nonvolatile memory of claim 25, wherein the plurality of trapping layer block structures comprises in sequence, a first oxide layer, a nitride layer, and a second oxide layer.

27. (New) The nonvolatile memory of claim 25, wherein the nonvolatile memory further comprises at least one dielectric disposed between the plurality of word lines and trapping layer block structures.

28. (New) The nonvolatile memory of claim 27, wherein the plurality of trapping layer block structures comprises in sequence, a first oxide layer, a nitride layer, and a second oxide layer.